



CORNERSTONE

Design guidelines for the tenth fabrication call – December 2018 Notification of intention to submit deadline – Friday 18th January 2019 Mask submission deadline – Friday 1st March 2019

File format = .gdsII.

Manufacturing grid size = 1 nm.

Design area = $11.47 \times 4.9 \text{ mm}^2$, with 0.5 mm bleed regions on the east and west facets if desired.

Top cell name: 'CellO_[Name of Institution]'.

1. Major changes to design submission process

For this call there are major changes to the design submission process (see Section 7 of CORNERSTONE 10th Call - Design Rules.pdf) to align with the introduction of the CORNERSTONE terms and conditions, which are available to download from the CORNERSTONE website:

www.cornerstone.sotonfab.co.uk/terms-and-conditions

All design submissions, even those that are supported by EPSRC funding, must agree with the terms and conditions. Under no circumstances will we accept designs without agreement with the terms.

Therefore, we strongly recommend that the terms and conditions are pre-authorised by your institution prior to the mask submission date.

Section 7 of the CORNERSTONE 10th Call - Design Rules.pdf document details the new design submission process in detail.

2. Design rule changes from previous 220 nm SOI platform call (MPW #8)

The following is a list of design rule changes from the previous 220 nm SOI platform design rules:

- 1. Minimum feature size for grating coupler layer (GDS layer 6) reduced to 200 nm. Minimum gap set as 250 nm for features up to 20 μ m long, and 300 nm for features longer than 20 μ m.
- 2. Minimum feature size for the waveguide layer (GDS layer 3) increased to 350 nm. Minimum gap reduced to 200 nm.
- 3. New 'labels' layer added as GDS layer 100. This layer will not have any design rule checking (DRC) performed on it and will be merged with Silicon Etch 2 by the CORNERSTONE team.
- 4. Target critical dimensions for each GDS layer added (Table 1).
- 5. Step-by-step details of the mask processing steps carried out by the CORNERSTONE team added (Section 8 of CORNERSTONE 10th Call Design Rules.pdf).
- 6. Standard single mode waveguide width for $\lambda = 1.55 \, \mu m$ increased to 450 nm.
- 7. 1x2 rib MMI length for λ = 1.55 μ m increased to 32.7 μ m.
- 8. Grating coupler design for $\lambda = 1.31 \,\mu m$ modified.

3. Design rules summary

A summary of the design rules and GDS layer numbers can be found in Table 1 below.





Table 1 – Design rules summary.

| | GDS | | Min. feature | Min. | Max. feature | Target critical |
|---------------------------------|--------|-------|-----------------|--------|-----------------|--------------------|
| Layer description | number | Field | size | gap | width | dimension |
| Silicon Etch 1 (70 nm ± 10 nm) | 6 | Dark | 200 nm | 250 nm | 20 μm | 315 nm |
| | | | 200 nm | 300 nm | N/a | |
| Silicon Etch 2 (120 nm ± 10 nm) | 3 | Light | 350 nm | 200 nm | N/a | 450 nm |
| | 4 | Dark | 200 nm | 350 nm | | |
| Silicon Etch 3 (100 nm to BOX) | 5 | Light | 250 nm | 250 nm | N/a | 250 nm |
| Heater Filaments | 39 | Light | 900 nm | 10 μm | N/a | 900 nm |
| Heater Contact Pads | 41 | Light | 2 μm | 10 μm | N/a | 2 μm |
| Bleed Area | 98 | N/a | N/a | N/a | N/a | N/a |
| Cell Outline | 99 | N/a | N/a | N/a | N/a | N/a |
| Labels* | 100 | Dark | 250 nm | 250 nm | N/a | N/a |

^{*}Features drawn in the Labels layer will be merged into Silicon Etch 2 by the CORNERSTONE team.

4. Minimum feature sizes, tolerances and other design rules

- Minimum feature sizes, minimum gaps, and maximum feature widths for each GDS layer are detailed in Table 1.
- The target critical dimension for each GDS layer is listed in Table 1. Note that other feature sizes may have a small dimension bias.
- \bullet A minimum spacing between waveguides of at least 5 μm is recommended to avoid power coupling.
- An overlap of at least 200 nm between GDS layers is essential to account for the alignment tolerance between layers.
- All structures drawn in GDS layer 6 (Grating couplers) must overlap by at least 200 nm with GDS layer 3 (Waveguides).
- All structures drawn in GDS layer 5 (Rib protect) should extend 10 μm beyond the edge of GDS layer 3 (Waveguides), with the exception of rib-to-strip transitions.
- An overlap of at least 10 μm between GDS layer 39 (Heater Filaments) and GDS layer 41 (Heater Contact Pads) is recommended for optimal heater performance.
- Ensure all structures drawn in GDS layer 6 (Grating couplers) do not overlap with either GDS layer 39 (Heater Filaments) or GDS 41 (Heater Contact Pads).
- All structures drawn in GDS layer 12 (Vias) must be inclusive of the metal contacts drawn in GDS layer 13 (Electrodes) by at least 500 nm (i.e. the electrode layer must extend in all directions at least 500 nm beyond the vias layer).
- An overlap of at least 10 μm between GDS layer 39 (Heater Filaments) and GDS layer 41 (Heater Contact Pads) is recommended for optimal heater performance.
- Ensure all structures drawn in GDS layer 6 (Grating couplers) do not overlap with either GDS layer 12 (Vias) or any of the metal/heater layers.

5. Technical support

For all queries, email cornerstone@soton.ac.uk.